

Amendments to the Claims

The following listing of claims replaces all other versions of claims previously presented.

Listing of Claims:

1-1.0 (Canceled)

11 (Currently Amended): ~~[[The]]~~ A method according to claim 10, of
chamfering a nitride semiconductor wafer comprising the steps of:

preparing a soft whetting apparatus having a long continually-fed elastic
tape and whetting granules of #300 to #5000 implanted on the elastic tape;

bringing the elastic tape into angular inscribing contact with an edge of
the circular nitride wafer with an angular contact angle of 40 degrees to 90
degrees at a pressure;

supplying the elastic tape with a whetting liquid which is powderless
water, powderless oil, powder including water, or powder including oil;

rotating the nitride wafer in the inscribing contact with the elastic tape;

feeding the elastic tape at a constant speed or varying speeds of 5 mm/min
to 60 mm/min in the angular direction around the wafer edge; and

abrading the edge of the wafer by the granules implanted on the soft
elastic tape into edge roughness of Ra5 μ m to Ra10nm, wherein the chamfering
method includes three steps, a first step uses a whettape of #300 to #1000, a
second step uses another whettape of #1000 to #2500 and a third step uses
another whettape of #2500 to #5000.

12 (Original): The method according to claim 11, wherein the first step employing a whettape of #800 produces an edge of roughness of $Ra0.9\mu m$, the second step employing a whettape of #2000 produces an edge of roughness of $Ra0.3\mu m$ and the third step employing a whettape of #3000 produces an edge of roughness of $Ra0.1\mu m$.

13-20 (Canceled)